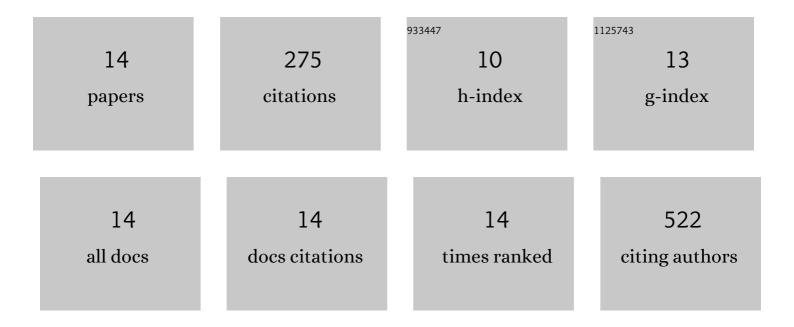
## Alessandra Leonhardt

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	A novel self-aligned double patterning integrated with Ga+ focused ion beam milling for silicon nanowire definition. Microelectronic Engineering, 2021, 237, 111493.	2.4	2
2	Understanding ambipolar transport in MoS <sub>2</sub> field effect transistors: the substrate is the key. Nanotechnology, 2021, 32, 135202.	2.6	14
3	Multicomponent Covalent Chemical Patterning of Graphene. ACS Nano, 2021, 15, 10618-10627.	14.6	31
4	Contact Interface Characterization of Graphene contacted MoS2 FETs. , 2021, , .		0
5	Graphene based Van der Waals contacts on MoS <sub>2</sub> field effect transistors. 2D Materials, 2021, 8, 015003.	4.4	15
6	Use of the Indirect Photoluminescence Peak as an Optical Probe of Interface Defectivity in MoS 2. Advanced Materials Interfaces, 2020, 7, 2000413.	3.7	10
7	Material-Selective Doping of 2D TMDC through Al <i><sub>x</sub></i> O <i><sub>y</sub></i> Encapsulation. ACS Applied Materials & Interfaces, 2019, 11, 42697-42707.	8.0	37
8	Devices and Circuits Using Novel 2-D Materials: A Perspective for Future VLSI Systems. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 1486-1503.	3.1	30
9	Relation between film thickness and surface doping of MoS2 based field effect transistors. APL Materials, 2018, 6, .	5.1	9
10	Growth of Millimeter-Sized Graphene Single Crystals on Al <sub>2</sub> O <sub>3</sub> (0001)/Pt(111) Template Wafers Using Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2018, 7, M195-M200.	1.8	20
11	The Role of Nonidealities in the Scaling of MoS <sub>2</sub> FETs. IEEE Transactions on Electron Devices, 2018, 65, 4635-4640.	3.0	14
12	Layer-controlled epitaxy of 2D semiconductors: bridging nanoscale phenomena to wafer-scale uniformity. Nanotechnology, 2018, 29, 425602.	2.6	48
13	(Invited) Internal Photoemission of Electrons from 2-Dimensional Semiconductors. ECS Transactions, 2017, 80, 191-201.	0.5	12
14	Improving MOCVD MoS <sub>2</sub> Electrical Performance: Impact of Minimized Water and Air Exposure Conditions. IEEE Electron Device Letters, 2017, 38, 1606-1609.	3.9	33